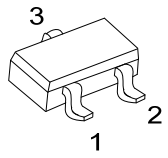
-0.3A, -150V P-CHANNEL POWER MOSFET



SOT-23
(EIAJ SC-59)

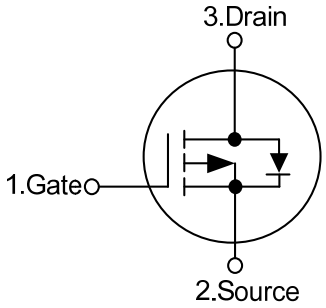
■ DESCRIPTION

The UTC **UF03P15** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed, cost-effectiveness and a minimum on-state resistance. It can also withstand high energy in the avalanche.

■ FEATURES

* $R_{DS(ON)} \leq 6.0\Omega$ @ V_{GS}=-10V, I_D=-0.2A
* Low capacitance
* Low gate charge
* Fast switching capability
* Avalanche energy specified

■ SYMBOL



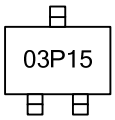
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF03P15L-AE3-R	UF03P15G-AE3-R	SOT-23	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

UF03P15G-AE3-R (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	-150	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I_D	-0.3	A
	Pulsed (Note 2)	I_{DM}	-1.2	A
Avalanche Current (Note 2)		I_{AR}	0.9	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	4.0	mJ
Power Dissipation		P_D	0.5	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 10mH, I_{AS} = 0.9A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C

■ THERMAL CHARACTERISTICS

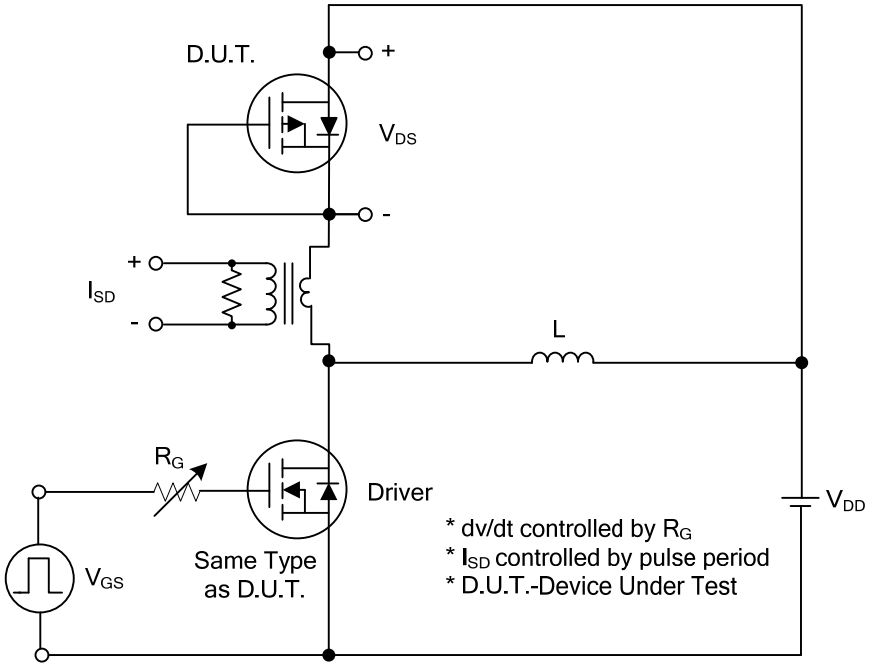
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	325	°C/W
Junction to Case	θ_{JC}	250	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

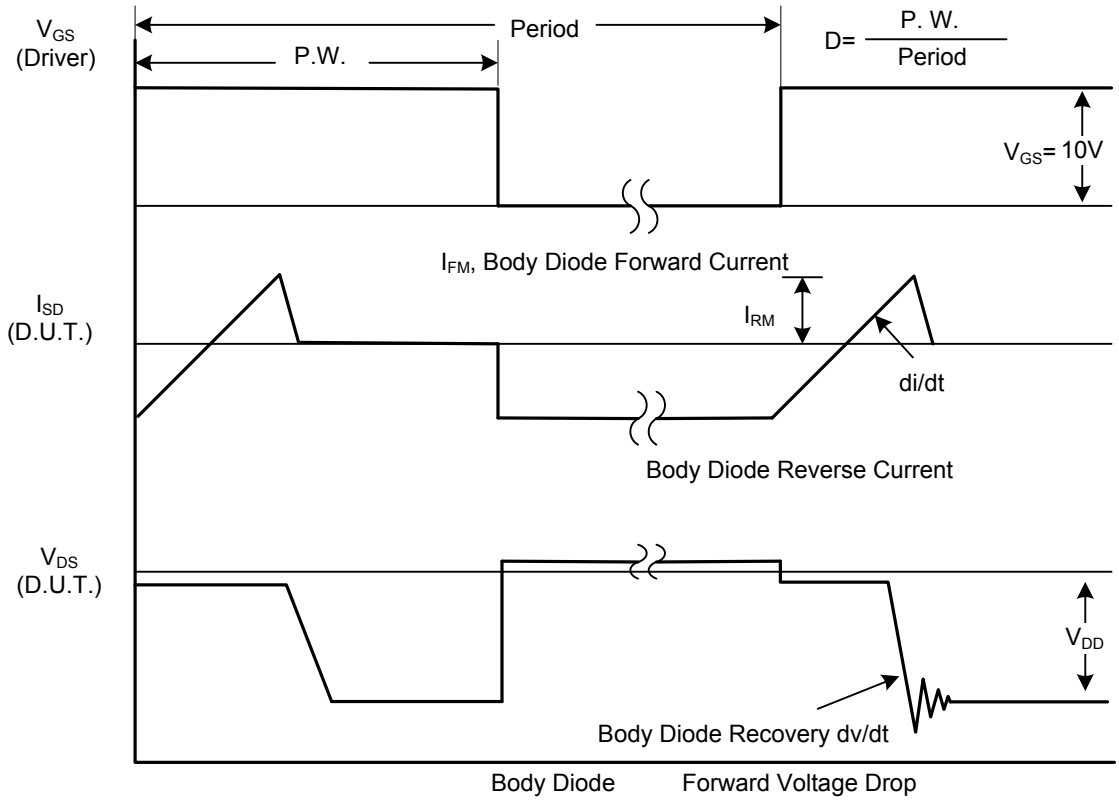
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0 V, I_D=-250μA	-150			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=-150V, V_{GS}=0V			-1	μA
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=-250μA	-2.0		-4.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-0.2A			6.0	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{DS}=-25V, V_{GS}=0V, f=1.0MHz		78		pF
Output Capacitance	C_{OSS}			21		pF
Reverse Transfer Capacitance	C_{RSS}			3.5		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	V_{DS}=-30V, V_{GS}=-10V, I_D=-0.3A I_G=-100μA (Note 1, 2)		8.8		nC
Gate Source Charge	Q_{GS}			1.2		nC
Gate Drain Charge	Q_{GD}			1.1		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	V_{DD}=-30V, V_{GS}=-10V, I_D=-0.3A, R_G=25Ω (Note 1, 2)		42		ns
Turn-ON Rise Time	t_R			48		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			53		ns
Turn-OFF Fall-Time	t_F					ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				-0.3	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				-1.2	A
Diode Forward Voltage (Note 1)	V_{SD}	I_S=-0.3A, V_{GS}=0V			-2.0	V

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

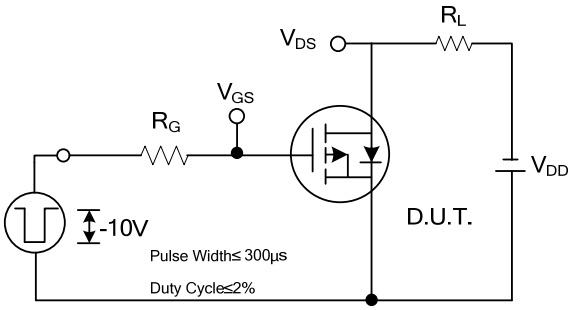


Peak Diode Recovery dv/dt Test Circuit

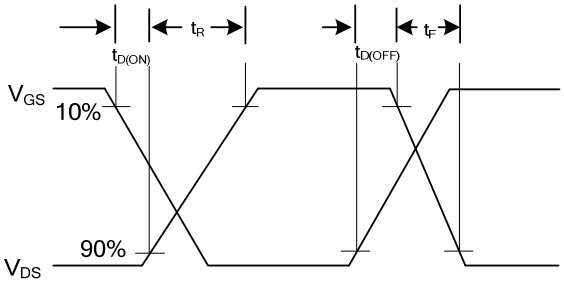


Peak Diode Recovery dv/dt Waveforms

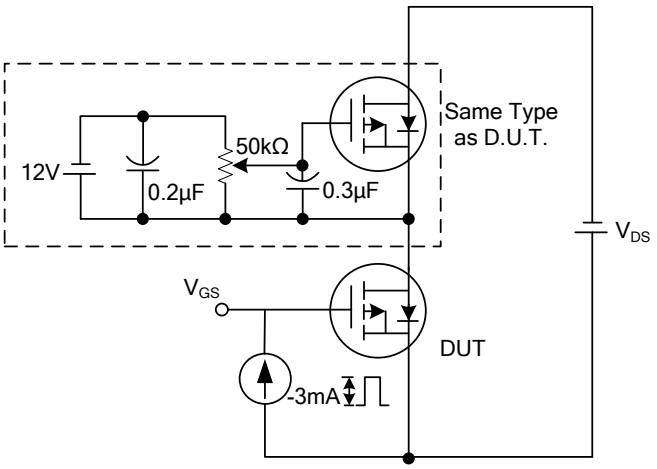
■ TEST CIRCUITS AND WAVEFORMS



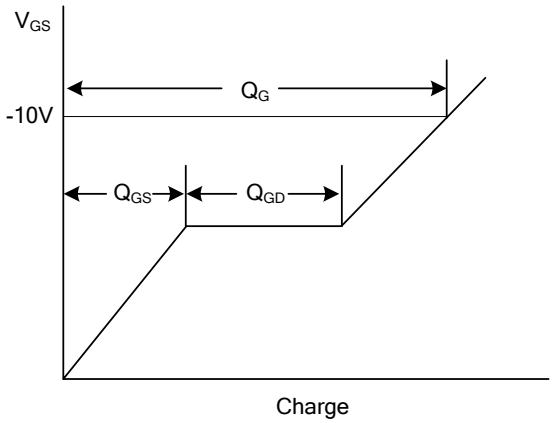
Switching Test Circuit



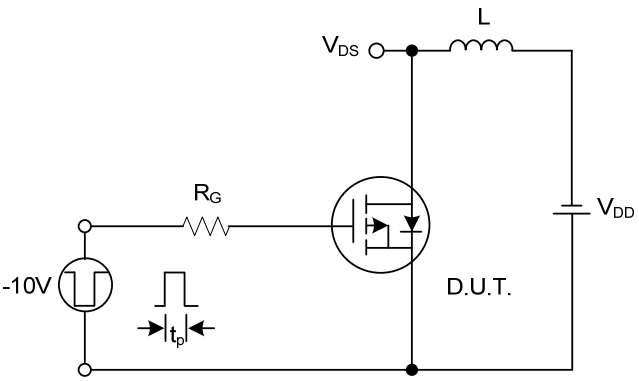
Switching Waveforms



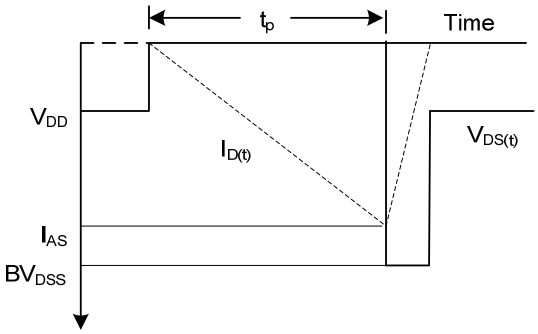
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms